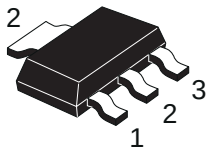
STN2NE10L

N - CHANNEL 100V - 0.33 Ω - 2A - SOT-223
STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STN2NE10L	100 V	< 0.4 Ω	2 A

- TYPICAL $R_{DS(on)}$ = 0.33 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- AVALANCHE RUGGED TECHNOLOGY
- 100 % AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION



SOT-223

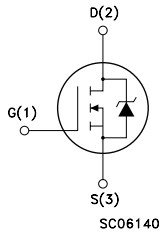
DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™ " stip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC MOTOR CONTROL (DISK DRIVES,etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	100	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	100	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (continuous) at T_c = 25 °C	2	A
I_D	Drain Current (continuous) at T_c = 100 °C	1.3	A
I_{DM}(•)	Drain Current (pulsed)	8	A
P_{tot}	Total Dissipation at T_c = 25 °C	2.5	W
	Derating Factor	0.02	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	6	V/ns
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area
New RDS (on) spec. starting from JULY 98

(1) $I_{SD} \leq 7$ A, di/dt ≤ 200 A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

THERMAL DATA

$R_{thj\text{-}pcb}$	Thermal Resistance Junction-PC Board Max	50	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient Max (Surface Mounted)	60	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose	260	^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	2	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 ^oC, $I_D = I_{AR}$, V_{DD} = 25 V)	20	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	100			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0) V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 ^oC				1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 1A V_{GS} = 5 V I_D = 1A		0.33 0.38	0.4 0.45	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	2			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 1 A	1.2	2.5		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0 V		345 45 20	450 60 25	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 50 V I_D = 3.5 A R_G = 4.7 Ω V_{GS} = 5 V		7 17	9 22	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 80 V I_D = 7 A V_{GS} = 5 V		10 5 4	14	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 80 V I_D = 7 A R_G = 4.7 Ω V_{GS} =5 V		8 9 19	10 12 25	ns ns ns

SOURCE DRAIN DIODE

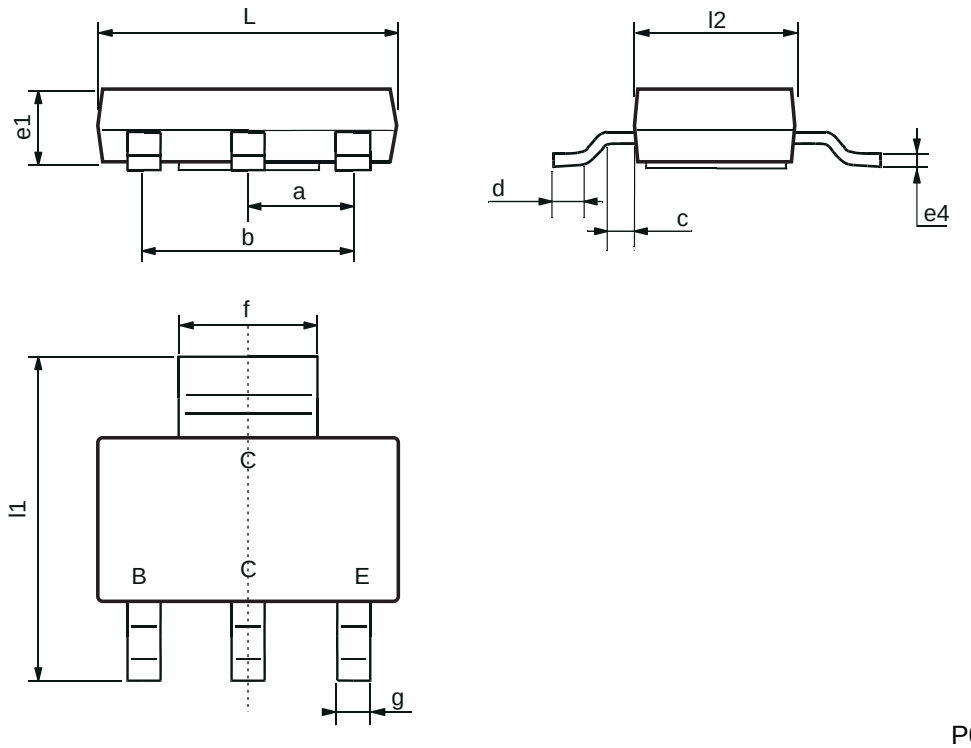
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				2 8	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 2 A V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 7 A di/dt = 100 A/µs V_{DD} = 30 V T_j = 150 °C		75 190 5		ns µC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

SOT-223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



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